ASSP For Power Management Applications

1-channel DC/DC Converter IC with Synchronous Rectifier

MB3885

DESCRIPTION

The MB3885 is a 1-channel DC/DC converter IC using pulse width modulation (PWM) and synchronous rectification, designed for down conversion applications.

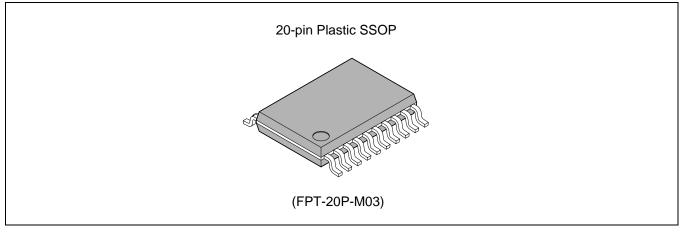
This device is a power supply with high output drive capacity. Synchronous rectification also provides for high efficiency.

In addition, a 5 V regulator is built in to reduce the number of system components. The result is an ideal built-in power supply for driving products with high speed CPU's such as home TV game devices and notebook PC's. This product is covered by US Patent Number 6,147,477.

FEATURES

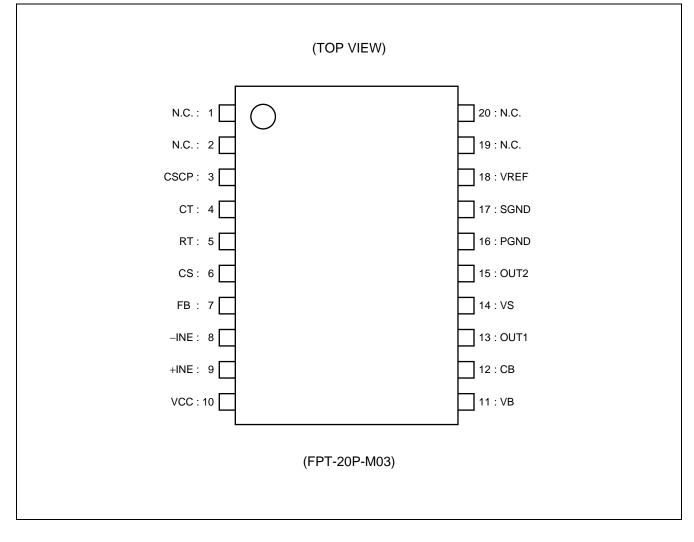
- Synchronous rectification for high efficiency
- Supply voltage range : 5.5 V to 18 V
- Built-in high-precision reference voltage circuit : 2.5 V \pm 1%
- Error Amp. threshold voltage $: 1.25 \text{ V} \pm 1\%$ (0 °C to 85 °C)
- Oscillator frequency range : 10 kHz to 500 kHz
- Built-in soft-start circuit with error Amp. input control
- Totem pole type output for N-ch MOSFET

PACKAGE





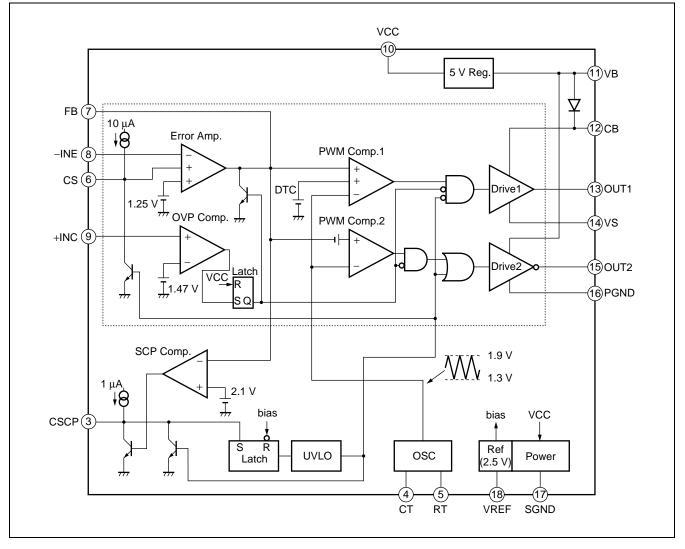
■ PIN ASSIGNMENTS



■ PIN DESCRIPTIONS

Pin No.	Symbol	I/O	Description
1	N.C.		No connection
2	N.C.		No connection
3	CSCP	_	Timer latch short protection capacitor connection terminal
4	СТ		Triangular wave oscillator frequency setting capacitor connection terminal
5	RT		Triangular wave oscillator frequency setting resistor connection terminal
6	CS		Soft-start capacitor connection terminal (Also used as output control)
7	FB	0	Error Amp. output terminal
8	-INE	I	Error Amp. inverted input terminal
9	+INC	I	Overvoltage comparator non-inverted input terminal
10	VCC		Reference voltage, control circuit power supply terminal
11	VB	0	Output circuit bias output terminal
12	СВ		Output bootstrap terminal Insert a capacitor between the CB and VS terminals, to bootstrap the IC in- ternal output transistor.
13	OUT1	0	Totem pole output terminal (External main side FET gate drive)
14	VS		External main side FET source connection terminal
15	OUT2	0	Totem pole output terminal. (External synchronous rectifier side FET gate drive)
16	PGND	_	Ground terminal
17	SGND		Ground terminal
18	VREF	0	Reference voltage output terminal
19	N.C.		No connection
20	N.C.		No connection

BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Rat	Unit	
Farameter	Symbol	Conditions	Min	Max	Unit
Supply voltage	Vcc	—		20	V
Boot voltage	Vсв	CB terminal		25	V
Output current	lo			120	mA
Peak output current	ЮР	$\begin{array}{l} Duty \leq 5\% \\ (t = 1 \ / \ fosc \times Duty) \end{array}$	_	800	mA
Power dissipation	PD	Ta ≤ +25 °C		555*	mW
Storage temperature	Tstg	—	-55	+125	°C

* : The package is mounted on the dual-sided epoxy board ($10cm \times 10cm$).

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

RECOMMENDED OPERATING CONDITIONS

Demonster	O week al	O an dition a		Value		11
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Supply voltage	Vcc	—	5.5	12	18	V
Boot voltage	Vсв	CB terminal			23	V
Reference voltage output current	lor	VREF terminal	-1		0	mA
Bias output current	Іов	VB terminal	-1		0	mA
	Vin	-INE terminal	0		Vcc - 1.8	V
Input voltage	VINC	+INC terminal	0	—	Vcc	V
Output current	lo	_	-100		100	mA
Peak output current	ЮР	Duty $\leq 5\%$ (t = 1 / fosc × Duty)	-700		700	mA
Oscillator frequency	fosc		10	200	500	kHz
Timing resistor	R⊤	_	6.8	10	12	kΩ
Timing capacitor	Ст	_	150	470	15000	pF
Boot capacitor	Св			0.1	1.0	μF
Reference voltage output capacitor	Cref	VREF terminal		0.1	1.0	μF
Bias output capacitor	Сув	VB terminal	1.0	4.7	10	μF
Soft-start capacitor	Cs	—		0.1	1	μF
Short detection capacitor	CSCP	—	_	0.01	0.1	μF
Operating ambient temperature	Та	—	-30	+25	+85	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

(VCC = 12 V, VB = 0 mA, VREF = 0 mA, Ta = +25 $^{\circ}$ C)

Parameter		Cumbal	Din No	Conditions		Value		Unit
Para	meter	Symbol	Pin No.	Conditions	Min	Тур	Мах	Unit
		Vref	18	Ta = +25 °C	2.475	2.500	2.525	V
1.	Output voltage	$\Delta V_{REF}/V_{REF}$	$1812 = 0$ °C to ± 85 °C			0.5*		%
Reference Voltage Block	Input stability	Line	18	VCC = 5.5 V to 18 V		1	10	mV
[Ref]	Load stability	Load	18	VREF = 0 mA to -1 mA		3	10	mV
	Short output current	los	18	VREF = 2 V	-28	-14	-7	mA
2. Bias Voltage Block [VB]	Output voltage	VB	11	_	4.95	5.05	5.15	V
3. Undervoltage	Threshold voltage	Vth	10	VCC = _	2.6	2.9	3.2	V
Lockout Circuit Block	Hysteresis width	Vн	10		_	0.2*		V
[UVLO]	Reset voltage	Vrst	10		1.7	2.1	2.5	V
4. Soft-start Block [CS]	Charge current	lcs	6		-14	-10	-6	μΑ
5. Short	Threshold voltage	Vтн	3	_	0.63	0.68	0.73	V
Detection Comparator	Input source current	ICSCP	3	—	-1.4	-1.0	-0.6	μΑ
Block [SCP]	Short detection time	t scp	3	CSCP = 0.01 μF	4.5	6.8	12.2	ms
6. Triangular	Oscillator frequency	fosc	4	$RT = 10 \text{ k}\Omega, CT = 470 \text{ pF}$	170	190	210	kHz
Wave Oscillator Block [OSC]	Frequency temperature variation rate	∆fosc/ fosc	4	Ta = 0 °C to +85 °C		1*		%
7. Error Amp	Threshold	Vth1	8	FB = 1.6 V, Ta = +25 °C	1.241	1.2500	1.259	V
	voltage	V _{TH2}	8	FB = 1.6 V, Ta = 0 °C to +85 °C	1.2375	1.2500	1.2625	V
Block [Error Amp.]	Input bias current	Ів	8	-INE = 0 V	-200	-20		nA
	Voltage gain	Av	7	DC	60	100		dB

* : Standard design value

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Parameter		Symbol Pin No. Conditions			Value		Unit	
				Conditions	Min	Тур	Max	Unit
	Frequency band width	BW	7	7 AV = 0 dB		800*	_	kHz
7.		Vfbh	7	—	2.2	2.5		V
Error Amp	Output voltage	Vfbl	7	—		0.8	1.0	V
Block [Error Amp.]	Output source current	ISOURCE	7	FB = 1.6 V		-100	-45	μΑ
	Output sink current	Isink	7	FB = 1.6 V	1.5	9.0		mA
8. PWM Comparator	Threshold	Vtl	7	Duty cycle = 0%	1.2	1.3	—	V
Block [PWM Comp.1, PWM Comp.2]	voltage	Vтн	7	Duty cycle = Dtr		1.81	2.0	V
9. Dead time Adjustment Block [DTC]	Maximum duty cycle	Dtr	13	RT = 10 kΩ, CT = 470 pF	85	90	95	%
	Output current	SOURCE1	13	$\begin{array}{l} Duty \leq 5\% \\ (t = 1 \; / \; fosc \times Duty) \end{array}$	_	-700*	_	mA
	(main side)	ISINK1	13	$\begin{array}{l} Duty \leq 5\% \\ (t = 1 \ / \ fosc \times Duty) \end{array}$		900*	_	mA
	Output voltage	Vон1	13	OUT1 = -100 mA, CB = 17 V, VS = 12 V	CB – 2.5	CB – 0.9	_	V
10. Output Block [Drive]	(main side)	Vol1	13	OUT1 = 100 mA, CB = 17 V, VS = 12 V		VS + 0.9	VS + 1.4	V
	Output current	ISOURCE2	15	$\begin{array}{l} Duty \leq 5\% \\ (t = 1 \; / \; fosc \times Duty) \end{array}$		-750*	_	mA
	(synchronous rectifier side)	Isink2	15	$\begin{array}{l} \text{Duty} \leq 5\% \\ (t=1 \ / \ \text{fosc} \times \text{Duty}) \end{array}$	_	900*		mA
	Output voltage	Vон2	15	OUT2 = -100 mA	2.5	4.1		V
	(synchronous rectifier side)	Vol2	15	OUT2 = 100 mA		1.0	1.4	V
	Diode voltage	VD	12	VB = 10 mA		0.9	1.1	V

(VCC = 12 V, VB = 0 mA, VREF = 0 mA, Ta = +25 $^{\circ}$ C)

* : Standard design value

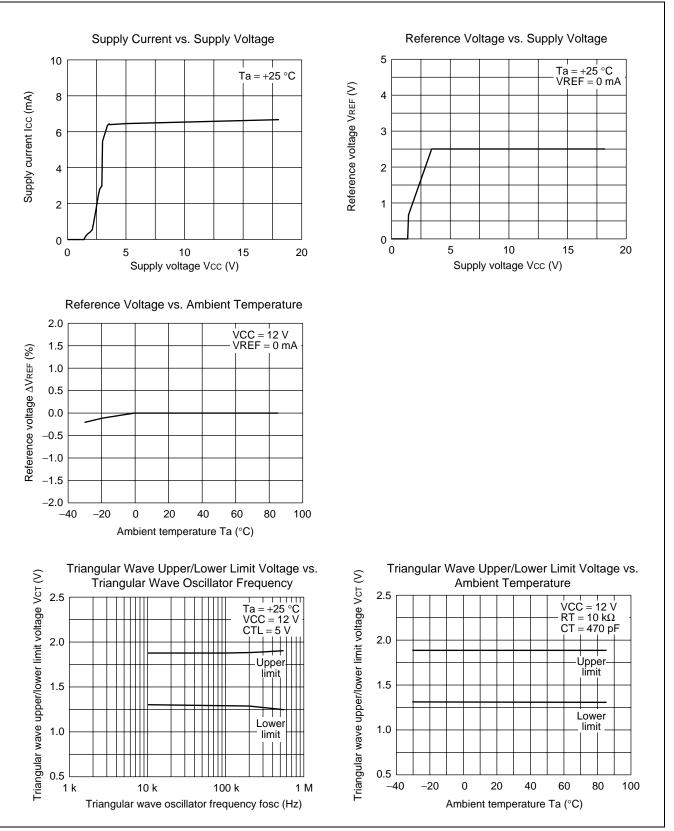
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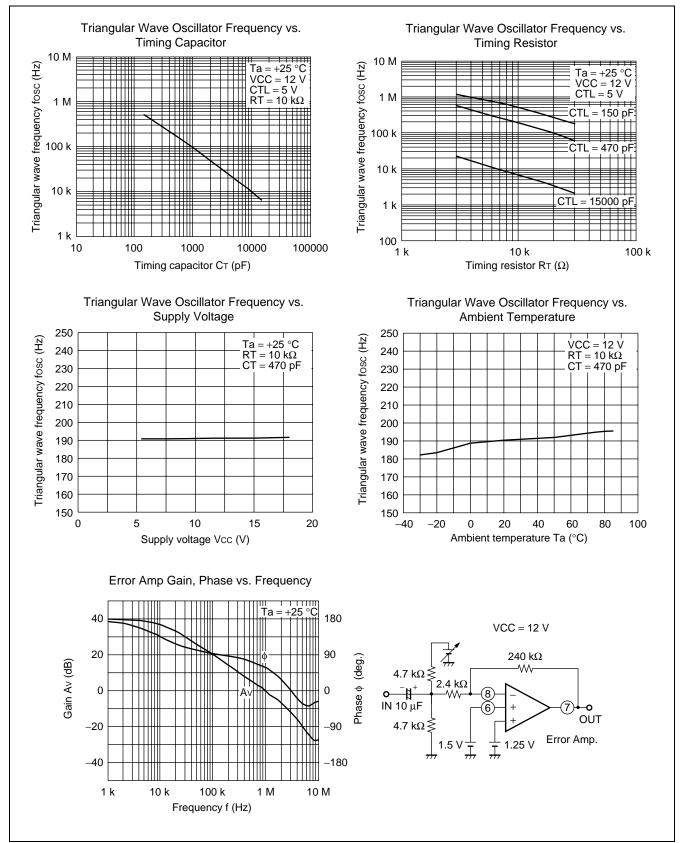
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(VCC = 12 V, VB = 0 mA, VREF = 0 mA, Ta = +25 $^{\circ}$ C)

Parameter		Symbol	Pin No.	Conditions	Value			Unit
		Symbol Fill No.		Conditions	Min	Тур	Max	Unit
10. Output		t ⊡1	13, 15	$\begin{array}{l} RT=10 \ k\Omega, \ CT=470 \ pF\\ OUT1=OUT2=OPEN,\\ VS=0 \ V\\ OUT2: \ V=OUT1: \ L\end{array}$	100	200		ns
Block Dead time [Drive]	t _{D2}	13, 13	$\begin{array}{l} RT=10 \ k\Omega, \ CT=470 \ pF\\ OUT1=OUT2=OPEN,\\ VS=0 \ V\\ OUT1: \ -OUT2: \ \checkmark \end{array}$	100	250		ns	
11. Overvoltage	Threshold voltage	Vтн	9	+INC = _√	1.44	1.47	1.50	V
Detection Comparator Block [OVP]	Input bias current	Ів	9	+INC = 0 V	-200	-30		nA
12. General	Power supply current	Icc	10	_		6.5	9.8	mA

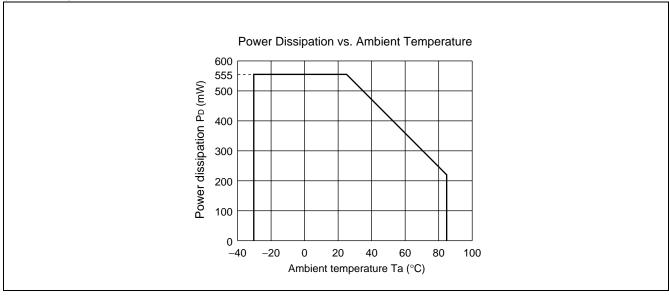
■ TYPICAL CHARACTERISTICS





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FUNCTION DESCRIPTION

1. DC/DC Converter Function

(1) Reference Voltage Block

The reference voltage circuit takes the voltage feed from the power supply terminal (pin 10) and generates a temperature compensated reference voltage (2.5 V Typ), for use as the reference voltage for the power supply control unit.

Also, an external load current can be obtained from the power supply at the VREF terminal (pin 18), up to a maximum of 1 mA.

(2) Triangular Wave Oscillator Block

A triangular waveform with amplitude 1.3 V to 1.9 V can be generated by connecting a timing capacitor and resistor to the CT terminal (pin 4) and RT terminal (pin 5), respectively.

The triangular oscillator waveform can be input to the IC's internal PWM comparator, as well as supplied externally from the CT terminal.

(3) Error Amp Block (Error Amp.)

The error Amp. is an amplifier that detects the output voltage from the DC/DC converter and outputs a PWM control signal. The error Amp. has a broad in-phase input voltage range of 0 to Vcc–1.8 V that can be easily set by the external power supply.

In addition, an arbitrary loop gain can be set up by connecting a feedback resistor and capacitor between the error Amp. output pin and inverter input pin, providing stable phase compensation to the system.

Also, power-on rush current can be prevented by connecting a soft-start capacitor between the error Amp. noninverted input pins CS terminal (pin 6). The soft-start function operates with a stable soft-start time that is not dependent on the output load of the DC/DC converter.

(4) PWM Comparator Block (PWM Comp.)

This is a voltage - pulse width modulator that controls the output duty according to the input voltage.

Main side : Turns the output FET on in the intervals in which the error Amp. output voltage is higher than the triangular wave voltage.

Synchronous rectifier side : Turns the output FET on in the intervals in which the triangular wave voltage the is lower than error Amp. voltage.

(5) Output Block

The output block has totem pole configuration on both the main side and synchronous rectifier side, and can drive an external N-ch MOSFET.

Also, the high output drive capability (700 mA Max : duty \leq 5%) provides high gate-source capacitor, enabling the use of low on-resistor FET devices.

2. Control Functions

Output ON/OFF control is provided by using the CS terminal (pin 6) setting functions.

Output On/Off Setting Functions

CS terminal voltage level	Output state
GND	OFF
Hi-Z	ON

3. Protective Functions

(1) Timer Latch Short Circuit Protection (SCP)

The short circuit protection comparators read the output voltage levels. If the output voltage falls below the short detection voltage, the timer circuit is activated to start charging the external capacitor Cscp connected to the CSCP terminal (pin 3).

When capacitor voltage reaches approximately 0.68 V the output FET turns off, setting the idle interval to 100%. Once the protection circuit is activated, it can be reset by turning the power supply off and on again. (See "Setting the Timer Latch Short Circuit Protector Time Constant.")

(2) Undervoltage Lockout Circuit Block (UVLO)

Transient status during normal power-on or momentary drops in supply voltage can cause abnormal operation in an control IC, leading to damage or degradation of system components. The undervoltage lockout circuit prevents such abnormal operations by reading the internal reference voltage level and switching the output FET off, setting the idle interval to 100% and holding the CSCP terminal (pin 3) to "L" level.

System operation is restored when the supply voltage rises back about the undervoltage lockout circuit threshold voltage.

(3) Overvoltage Protection Block (OVP)

The overvoltage protection circuit uses an overvoltage comparator (OVP Comp.) to read the output voltage levels from the DC/DC converter. If the output voltage exceeds the threshold voltage a latch is set, turning off the main side FET.

Once the protector circuit is activated, it can be reset by switching the power supply off and on again.

■ SETTING THE TIMER LATCH SHORT CIRCUIT PROTECTOR TIME CONSTANT

The error Amp. output level constantly compares operation with the short circuit protection comparator as the reference voltage.

When the DC/DC comparator load conditions are stable, the short circuit protection comparator output is at "H" level, transistor Q1 is on, and the CSCP terminal (pin 3) is held at input standby voltage $(\sqrt{2\pi r} + 50 \text{ m})$

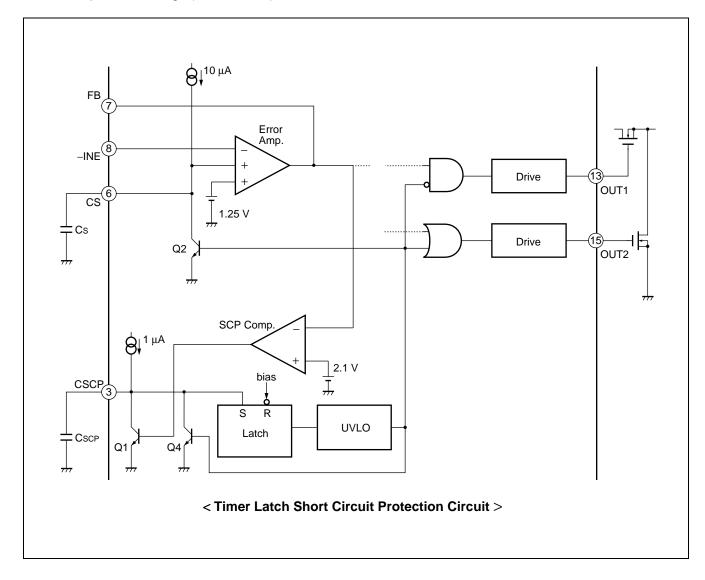
 $(V_{STB}: = 50 \text{ mV})$.

If load conditions change rapidly, such as during a load short, causing output voltage to drop, the short circuit protection comparator output goes to "L" level. This causes the transistor Q1 to shut off, charging the short circuit protection capacitor Cscp (connected to the CSCP terminal) at 1 μ A.

Short detection time

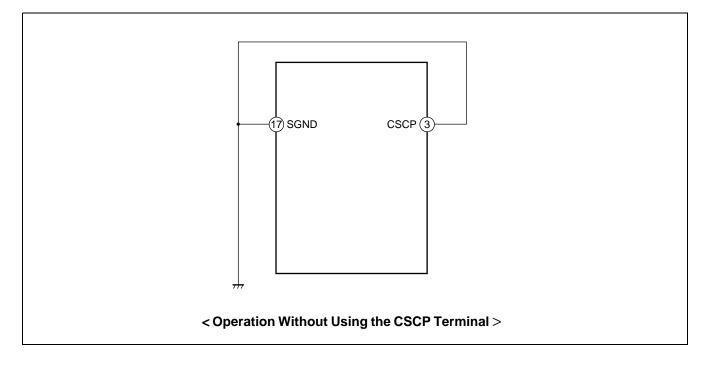
tscp (s) \Rightarrow 0.68 × Cscp (μ F)

When the capacitor Cscp is charted to the threshold voltage (V_{TH} : = 0.68 V) a latch is set, turning the external FET off (setting the idle interval to 100%). At this time the latch input is closed and the CSCP terminal is held at the input latch voltage (V_I : = 50 mV).



PROCESSING WITHOUT USING THE CSCP TERMINAL

When the timer latch short circuit protection circuit is not used, the CSCP terminal (pin 3) should be shorted to SGND using the shortest possible connection.



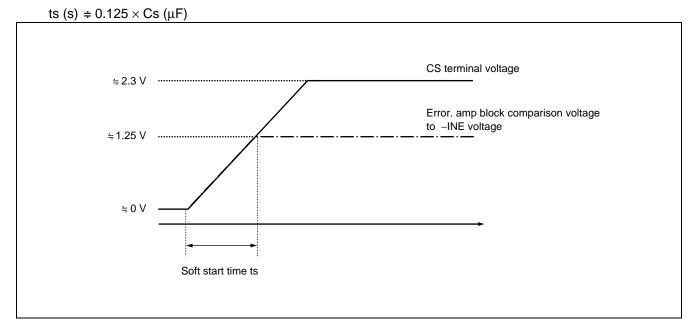
SOFT-START TIME SETTING

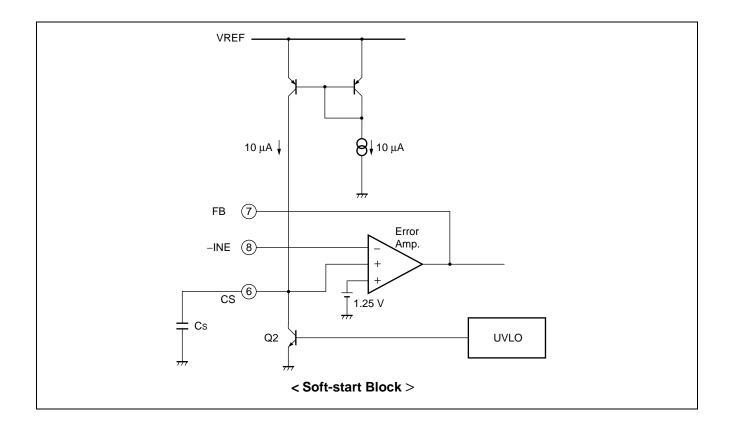
The soft-start function prevents rush current events when the IC power is turned on, by connecting soft-start capacitors (Cs) to the CS terminal (pin 6).

When the IC is activated (Vcc \ge UVLO threshold voltage), Q2 is off and the CS terminals begin charging the externally connected soft-start capacitors (Cs) at 10 μ A.

Because the error Amp. output (FB) is determined by the ratio of the lower of the two non-inverted input terminals (1.25 V, CS terminal voltage) to the inverted input terminal voltage (-INE), the soft-start interval (when CS terminal voltage < 1.25 V) FB is determined by the ratio of the -INE terminal voltage and CS terminal voltage. Thus the DC/DC converter output voltage is in proportion to the rise in the CS terminal voltage as the soft-start capacitor connected to the CS terminal charges. The soft-start time is determined by the following formula.

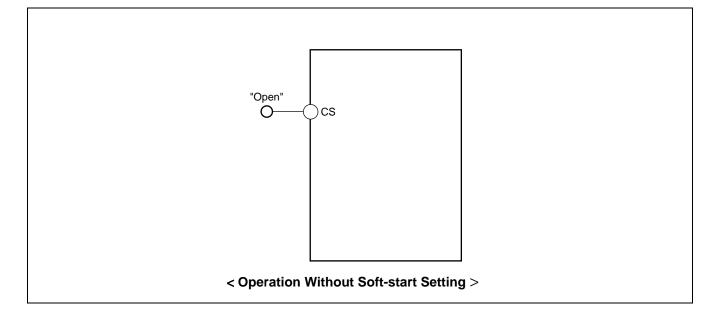
Soft-start time (time to output 100%)





PROCESSING WITHOUT USING THE CS TERMINALS

When the soft-start function is not used, the CS terminal (pin 6) should be left open.



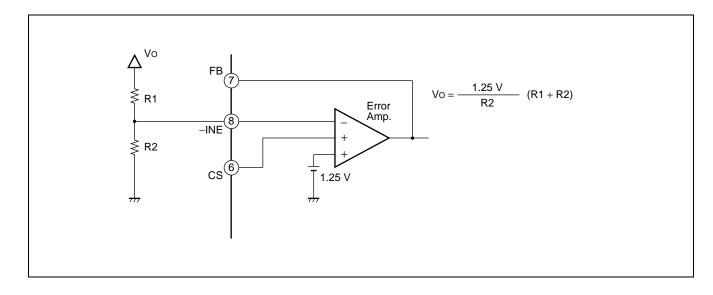
OSCILLATOR FREQUENCY SETTING

The oscillator frequency can be set by connecting a timing capacitor (C_T) to the CT terminal (pin 4) and a timing resistor (R_T) to the RT terminal (pin 5).

Oscillator frequency

fosc (kHz) $\Rightarrow \frac{893000}{C_{T} (pF) \bullet R_{T} (k\Omega)}$





OVERVOLTAGE PROTECTION CIRCUIT VOTAGE SETTING

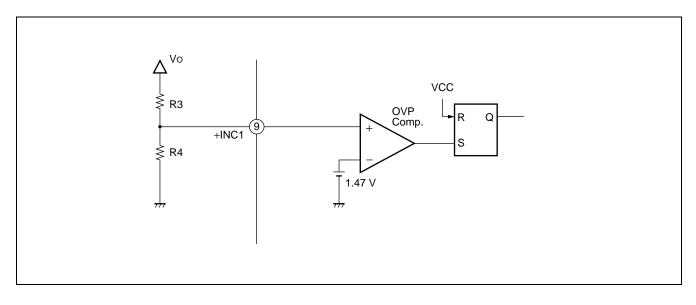
Overvoltage conditions in the DC/DC converter output voltage can be detected by connecting external resistance from the DC/DC converter output voltage to the +INC terminal (pin 9) on the respective overvoltage protection comparator circuits (OVP comp.) .

When the output voltage of the DC/DC converter rises above the detection voltage, the overvoltage protection comparator (OVP Comp.) output goes to "H" level, setting a latch and shutting off.

Detection voltage

 $V_{OVP}(V) = 1.47 \times (R3 + R4) / R4$

Once the protection circuit has been activated, it can be reset by lowering the VCC voltage below the reset voltage (1.7 V Min) .



PRECAUTIONS RELATED TO SUPPLY VOLTAGE RANGE

Although the supply voltage range listed under recommended operating requirements is 5.5V-18V, generation of heat limits the maximum operating supply voltage since the IC's internal loss varies with the frequency of oscillation and FET's total gate charge. When using the MB 3885 in an application, caution must be taken in relation to supply voltage range.

As shown below, I_B (average current) can be determined from the total gate charge Qg₁, Qg₂, charged from the gate capacitance (C_{iss1}, C_{iss2}, C_{rss1}, C_{rss2}) of the external FET Q1, Q2, by the following formula.

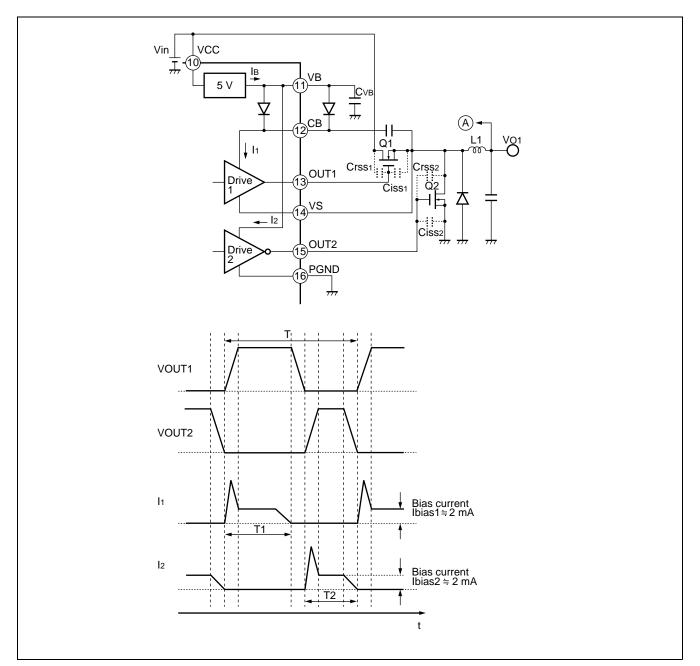
$$I_{B}(A) = I_{1} + I_{2}$$

 $= Ibias_1 \times \quad \frac{T1}{T} + \frac{Qg_1}{T} + Ibias_2 \times \frac{T2}{T} + \frac{Qg_2}{T} \quad (Ibias_1 = Ibias_2 \doteqdot 2 \text{ mA})$

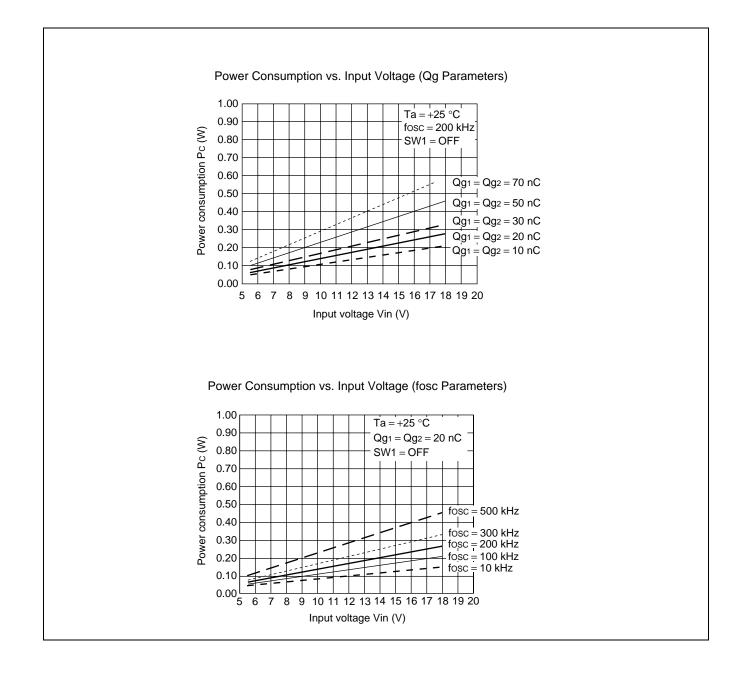
Because IC current consumption other than I_B is 6.5 mA, power consumption can be determined from the following formula.

Power consumption : Pc

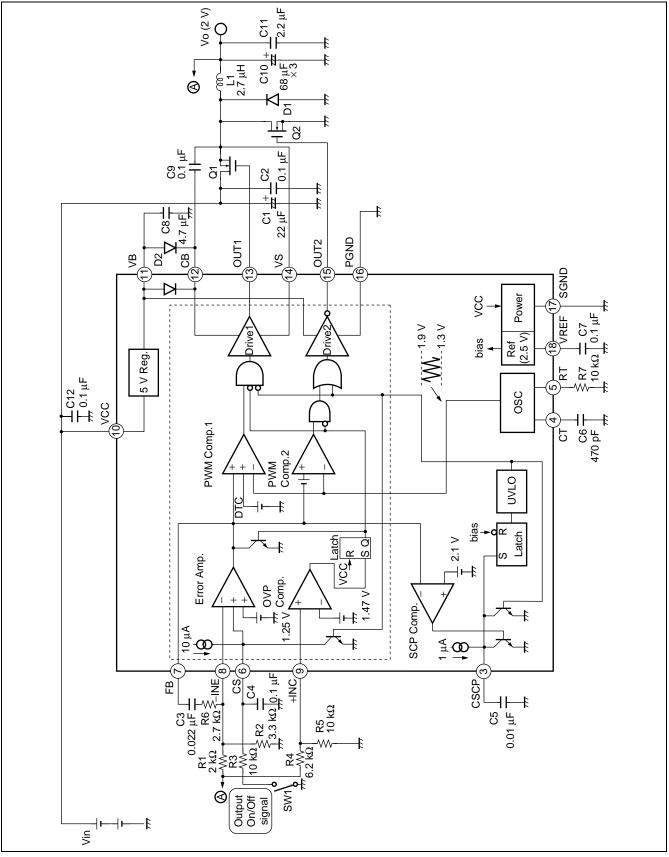
Pc (W) \Rightarrow 0.0065 × Vcc + Vcc × I_B - 1 / 2 × V_B × I_B



Using the above formulas to determine power consumption, settings should be made with reference to the "Power Consumption vs. Input Voltage" on the following page, as well as the "Power dissipation vs. Ambient Temperature."



■ APPLICATION CIRCUIT



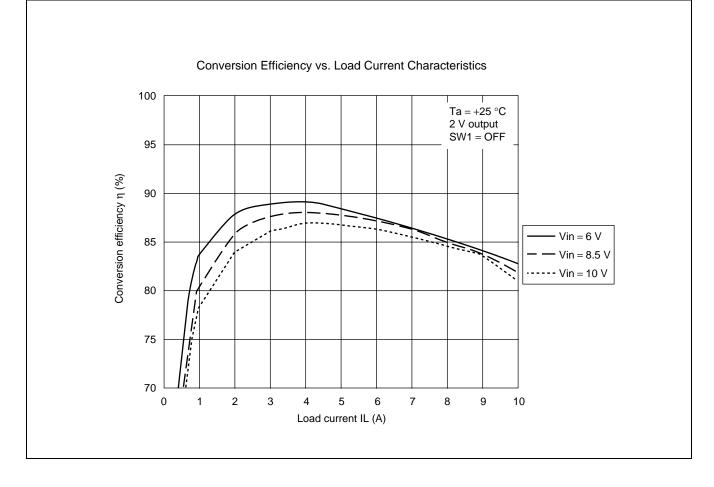
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■ COMPONENT LIST

COMPONENT	ITEM	SPECIF	SPECIFICATION		PARTS No.
Q1, Q2	FET	VDS = 30 V, Q	g = 23 nC (Max)	IR	IRF7811
D1	Diode	VF = 0.35 V (N	lax) , at IF = 1 A	ROHM	RB051L-40
D2	Diode	VF = 0.3 V (Max	<) , at IF = 10 mA	ROHM	RB495D
L1	Coil	2.7 μΗ	12 A, 4.5 mΩ	TDK	RLF12545T -2R7N8R7
C1	OS Condenser	22 μF	25 V		
C2	Ceramics Condenser	0.1 μF	25 V		
C3	Ceramics Condenser	0.022 μF	25 V		
C4	Ceramics Condenser	0.1 μF	25 V		
C5	Ceramics Condenser	0.01 μF	10 V		
C6	Ceramics Condenser	470 pF	50 V		
C7	Ceramics Condenser	0.1 μF	25 V		
C8	Ceramics Condenser	4.7 μF	10 V		
C9	Ceramics Condenser	0.1 μF	25 V		
C10	Electrolytic Condenser	68 μF	6.3 V		
C11	Ceramics Condenser	2.2 μF	6.3 V		
C12	Ceramics Condenser	0.1 μF	25 V		
R1	Resistor	2 kΩ	1/4 W		
R2	Resistor	3.3 kΩ	1/4 W		
R3	Resistor	10 kΩ	1/4 W		
R4	Resistor	6.2 kΩ	1/4 W		—
R5	Resistor	10 kΩ	1/4 W		
R6	Resistor	2.7 kΩ	1/4 W		
R7	Resistor	10 kΩ	1/4 W		

Notes : IR : International Rectifier Corp. ROHM : Rohm, Ltd. TDK : TDK, Ltd.

■ REFERENCE DATA



PRECAUTIONARY INFORMATION

- Printed circuit board ground lines should be designed with consideration for common impedance.
- Take sufficient countermeasures should be taken to protect against static electricity.
- Always place semiconductors in containers that have anti-static provisions, or are conductive.
- After mounting, PC boards should be placed in conductive bags or containers for storage and handling.
- Working surfaces, tools, and measurement equipment should be grounded.
- Persons handling semiconductors should be grounded directly with resistance of 250 k Ω to 1 M Ω .

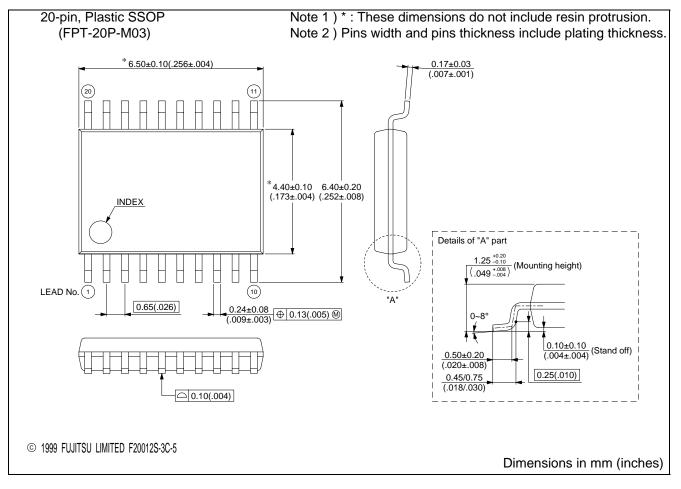
• Do not apply negative voltages.

• Application of negative voltage of -0.3 V or greater can create parasitic transistor effects on an LSI device, leading to abnormal operation.

ORDERING INFORMATION

Part Number	Package	Remarks
MB3885PFV	Plastic SSOP 20-pin (FPT-20P-M03)	

■ PACKAGE DIMENSION



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